

**Qxx40xx Series**



**Agency Approval**

Agency	Agency File Number
	K & J Packages: E71639

**Main Features**

Symbol	Value	Unit
$I_{T(RMS)}$	40	A
$V_{DRM}/V_{RRM}$	400 to 1000	V
$I_{GT(Q1)}$	50 to 100	mA

**Schematic Symbol**



**Description**

The 40 Amp bi-directional solid state switch series is designed for AC switching and phase control applications such as motor speed, temperature modulation controls, lighting controls, and static switching relays.

Alternistor type devices only operate in quadrants I, II, & III and are used in circuits requiring high dv/dt capability.

**Features & Benefits**

- RoHS Compliant
- Glass – passivated junctions
- Voltage capability up to 1000V
- Surge capability up to 400A
- Electrically isolated K & J -Packages are UL recognized for 2500Vrms

**Applications**

Excellent for AC switching and phase control applications such as heating, lighting, and motor speed controls.

Typical applications are AC solid-state switches, industrial power tools, exercise equipment, white goods and commercial appliances.

Alternistor Triacs (no snubber required) are used in applications with extremely inductive loads requiring highest commutation performance.

Internally constructed isolated packages are offered for ease of heat sinking with highest isolation voltage.

**Additional Information**



**Datasheet**



**Resources**



**Samples**

### Absolute Maximum Ratings — Alternistor Triac (3 Quadrants)

Symbol	Parameter			Value	Unit
$I_{T(RMS)}$	RMS on-state current (full sine wave)	Qxx40x7 Qxx40xH6	$T_C = 75^\circ\text{C}$	40	A
$I_{TSM}$	Non repetitive surge peak on-state current (full cycle, $T_J$ initial = $25^\circ\text{C}$ )	f = 50 Hz	t = 20 ms	335	A
		f = 60 Hz	t = 16.7 ms	400	
$I^2t$	I <sup>2</sup> t Value for fusing		$t_p = 8.3$ ms	664	A <sup>2</sup> s
di/dt	Critical rate of rise of on-state current ( $I_G = 2 \times I_{GT}$ , tr ≤ 100 ns)	f = 120 Hz	$T_J = 125^\circ\text{C}$	150	A/μs
$I_{GTM}$	Peak gate trigger current	$t_p \leq 10$ μs $I_{GT} \leq I_{GTM}$	$T_J = 125^\circ\text{C}$	4	A
$P_{G(AV)}$	Average gate power dissipation		$T_J = 125^\circ\text{C}$	0.8	W
$T_{stg}$	Storage temperature range			-40 to 150	°C
$T_J$	Operating junction temperature range			-40 to 125	°C

Note: xx = voltage, x = package

### Electrical Characteristics ( $T_J = 25^\circ\text{C}$ , unless otherwise specified) — Alternistor Triac (3 Quadrants)

Symbol	Test Conditions	Quadrant		Value			Unit
				Qxx40xH6	Qxx40K5	Qxx40x7	
$I_{GT}$	$V_D = 12\text{V}$ $R_L = 60 \Omega$	I – II – III	MAX.	80	50	100	mA
$V_{GT}$	$V_D = 12\text{V}$ $R_L = 60 \Omega$	I – II – III	MAX.	1.3	1.3	2.0	V
$V_{GD}$	$V_D = V_{DRM}$ $R_L = 3.3 \text{k}\Omega$ $T_J = 125^\circ\text{C}$	I – II – III	MIN.	0.2			V
$I_H$	$I_T = 400\text{mA}$		MAX.	80	75	100	mA
dv/dt	$V_D = V_{DRM}$ Gate Open $T_J = 125^\circ\text{C}$	400V	MIN.	600	500	700	V/μs
		600V		500	475	625	
		800V		475	400	575	
	$V_D = V_{DRM}$ Gate Open $T_J = 100^\circ\text{C}$	1000V			--	500	
(dv/dt)c	(di/dt)c = 21.6 A/ms $T_J = 125^\circ\text{C}$		MIN.	30	20	50	V/μs
$t_{gt}$	$I_G = 2 \times I_{GT}$ PW = 15μs $I_T = 56.6\text{A(pk)}$		TYP.	5			μs

### Static Characteristics

Symbol	Test Conditions			Value	Unit	
$V_{TM}$	$I_{TM} = 56.6\text{A}$ $t_p = 380 \mu\text{s}$	$T_J = 25^\circ\text{C}$	MAX.	1.8	V	
$I_{RRM}^{DRM}$	$V_D = V_{DRM} / V_{RRM}$	$T_J = 25^\circ\text{C}$	400 – 1000V	MAX.	20	μA
		$T_J = 125^\circ\text{C}$	400 – 800V	MAX.	5	mA
		$T_J = 100^\circ\text{C}$	1000V	MAX.	5	mA

### Thermal Resistances

Symbol	Parameter		Value	Unit
$R_{\theta(J-C)}$	Junction to case (AC)	Qxx40KH6 Qxx40K5 Qxx40K7	0.97	°C/W
		Qxx40JH6 Qxx40J7	0.95	

Note: xx = voltage

**Figure 1: Definition of Quadrants**

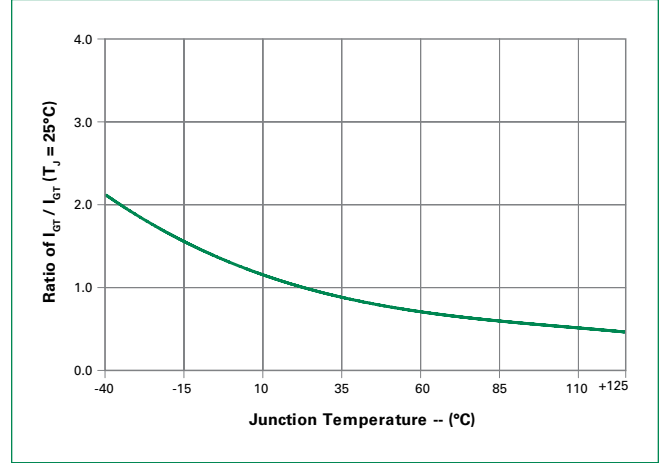


Note: Alternistors will not operate in QIV

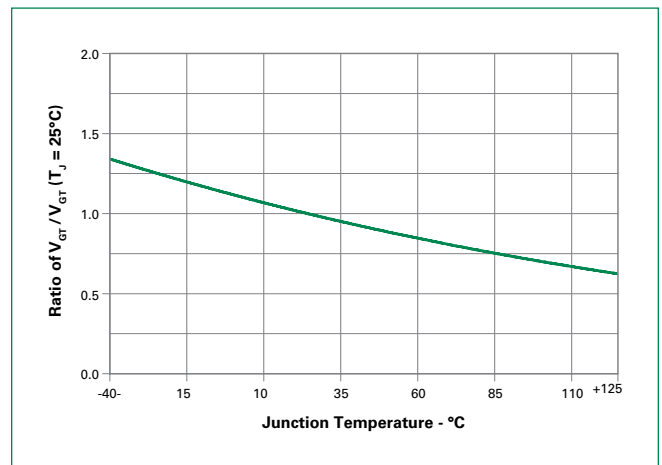
**Figure 3: Normalized DC Holding Current vs. Junction Temperature**



**Figure 2: Normalized DC Gate Trigger Current for All Quadrants vs. Junction Temperature**



**Figure 4: Normalized DC Gate Trigger Voltage for All Quadrants vs. Junction Temperature**



**Figure 5: Power Dissipation (Typical) vs. RMS On-State Current**



**Figure 6: Maximum Allowable Case Temperature vs. On-State Current**



**Figure 7: On-State Current vs. On-State Voltage (Typical)**



**Figure 8: Surge Peak On-State Current vs. Number of Cycles**



Note: xx = voltage

### Soldering Parameters

Reflow Condition		Pb – Free assembly
Pre Heat	- Temperature Min ( $T_{s(min)}$ )	150°C
	- Temperature Max ( $T_{s(max)}$ )	200°C
	- Time (min to max) ( $t_s$ )	60 – 180 secs
Average ramp up rate (Liquidus Temp) ( $T_L$ ) to peak		5°C/second max
$T_{s(max)}$ to $T_L$ - Ramp-up Rate		5°C/second max
Reflow	- Temperature ( $T_L$ ) (Liquidus)	217°C
	- Time (min to max) ( $t_s$ )	60 – 150 seconds
Peak Temperature ( $T_p$ )		260 <sup>+0/-5</sup> °C
Time within 5°C of actual peak Temperature ( $t_p$ )		20 – 40 seconds
Ramp-down Rate		5°C/second max
Time 25°C to peak Temperature ( $T_p$ )		8 minutes Max.
Do not exceed		280°C



### Physical Specifications

<b>Terminal Finish</b>	100% Matte Tin-plated.
<b>Body Material</b>	UL recognized epoxy meeting flammability classification 94V-0.
<b>Lead Material</b>	Copper Alloy

### Design Considerations

Careful selection of the correct device for the application's operating parameters and environment will go a long way toward extending the operating life of the Thyristor. Good design practice should limit the maximum continuous current through the main terminals to 75% of the device rating. Other ways to ensure long life for a power discrete semiconductor are proper heat sinking and selection of voltage ratings for worst case conditions. Overheating, overvoltage (including  $dv/dt$ ), and surge currents are the main killers of semiconductors. Correct mounting, soldering, and forming of the leads also help protect against component damage.

### Environmental Specifications

Test	Specifications and Conditions
<b>AC Blocking</b>	MIL-STD-750, M-1040, Cond A Applied Peak AC voltage @ 125°C for 1008 hours
<b>Temperature Cycling</b>	MIL-STD-750, M-1051, 100 cycles; -40°C to +150°C; 15-min dwell-time
<b>Temperature/Humidity</b>	EIA / JEDEC, JESD22-A101 1008 hours; 320V - DC: 85°C; 85% rel humidity
<b>High Temp Storage</b>	MIL-STD-750, M-1031, 1008 hours; 150°C
<b>Low-Temp Storage</b>	1008 hours; -40°C
<b>Resistance to Solder Heat</b>	MIL-STD-750 Method 2031
<b>Solderability</b>	ANSI/J-STD-002, category 3, Test A
<b>Lead Bend</b>	MIL-STD-750, M-2036 Cond E

**Dimensions — TO-218X (J Package) — Isolated Mounting Tab**



Dimension	Inches		Millimeters	
	Min	Max	Min	Max
A	0.810	0.835	20.57	21.21
B	0.610	0.630	15.49	16.00
C	0.178	0.188	4.52	4.78
D	0.055	0.070	1.40	1.78
E	0.487	0.497	12.37	12.62
F	0.635	0.655	16.13	16.64
G	0.022	0.029	0.56	0.74
H	0.075	0.095	1.91	2.41
J	0.575	0.625	14.61	15.88
K	0.256	0.264	6.50	6.71
L	0.220	0.228	5.58	5.79
M	0.080	0.088	2.03	2.24
N	0.169	0.177	4.29	4.49
P	0.034	0.042	0.86	1.07
R	0.113	0.121	2.87	3.07
S	0.086	0.096	2.18	2.44
T	0.156	0.166	3.96	4.22
U	0.161	0.165	4.10	4.20
V	0.603	0.618	15.31	15.70
W	0.000	0.005	0.00	0.13
X	0.003	0.012	0.07	0.30
Y	0.028	0.032	0.71	0.81
Z	0.085	0.095	2.17	2.42

**Dimensions — TO-218AC (K Package) — Isolated Mounting Tab**



Dimension	Inches		Millimeters	
	Min	Max	Min	Max
A	0.810	0.835	20.57	21.21
B	0.610	0.630	15.49	16.00
C	0.178	0.188	4.52	4.78
D	0.055	0.070	1.40	1.78
E	0.487	0.497	12.37	12.62
F	0.635	0.655	16.13	16.64
G	0.022	0.029	0.56	0.74
H	0.075	0.095	1.91	2.41
J	0.575	0.625	14.61	15.88
K	0.211	0.219	5.36	5.56
L	0.422	0.437	10.72	11.10
M	0.058	0.068	1.47	1.73
N	0.045	0.055	1.14	1.40
P	0.095	0.115	2.41	2.92
Q	0.008	0.016	0.20	0.41
R	0.008	0.016	0.20	0.41
U	0.161	0.165	4.10	4.20
W	0.085	0.095	2.17	2.42

**Product Selector**

Part Number	Voltage				Gate Sensitivity Quadrants		I <sub>T(RMS)</sub>	Type	Package
	400V	600V	800V	1000V	I – II – III	IV			
Qxx40KH6	X	X	X	X	80mA		40A	Alternistor Triac	TO-218AC
Qxx40JH6	X	X	X		80mA		40A	Alternistor Triac	TO-218X
Qxx40K5	X	X	X		50mA		40A	Alternistor Triac	TO-218AC
Qxx40K7	X	X	X	X	100 mA		40A	Alternistor Triac	TO-218AC
Qxx40J7	X	X	X		100 mA		40A	Alternistor Triac	TO-218X

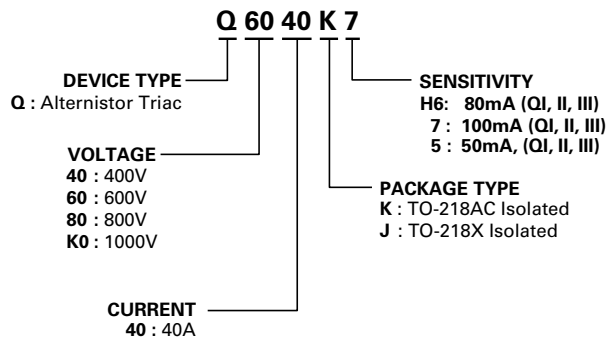
Note: xx = Voltage

**Packing Options**

Part Number	Marking	Weight	Packing Mode	Base Quantity
Qxx40KH6TP	Qxx40KH6	4.40g	Tube	250 (25 per tube)
Qxx40JH6TP	Qxx40JH6	5.23g	Tube	250 (25 per tube)
Qxx40K5TP	Qxx40K5	4.40g	Tube	250 (25 per tube)
Qxx40K7TP	Qxx40K7	4.40g	Tube	250 (25 per tube)
Qxx40J7TP	Qxx40J7	5.23g	Tube	250 (25 per tube)

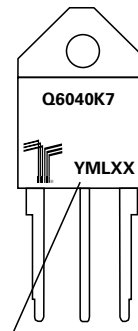
Note: xx = Voltage

**Part Numbering System**



**Part Marking System**

TO-218 AC - (K Package)  
TO-218 X - (J Package)



Date Code Marking  
Y: Year Code  
M: Month Code  
L: Location Code  
XX: Lot Serial Code

## Данный компонент на территории Российской Федерации

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Сотрудничество с глобальными дистрибьюторами электронных компонентов, предоставляет возможность заказывать и получать с международных складов практически любой перечень компонентов в оптимальные для Вас сроки.

На всех этапах разработки и производства наши партнеры могут получить квалифицированную поддержку опытных инженеров.

Система менеджмента качества компании отвечает требованиям в соответствии с ГОСТ Р ИСО 9001, ГОСТ РВ 0015-002 и ЭС РД 009

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